Technical University of Denmark



## Fabrication of Al-doped ZnO high aspect ratio nanowires and trenches as active components in mid-infrared plasmonics

Shkondin, Evgeniy; Takayama, Osamu; Larsen, Pernille Voss; Mar, Mikkel Dysseholm; Jensen, Flemming; Lavrinenko, Andrei

Publication date: 2016

Document Version Publisher's PDF, also known as Version of record

Link back to DTU Orbit

Citation (APA):

Shkondin, E., Takayama, O., Larsen, P. V., Mar, M. D., Jensen, F., & Lavrinenko, A. (2016). Fabrication of Aldoped ZnO high aspect ratio nanowires and trenches as active components in mid-infrared plasmonics. Abstract from 16th Atomic Layer Deposition Conference, Dublin, Ireland.

## DTU Library Technical Information Center of Denmark

## **General rights**

Copyright and moral rights for the publications made accessible in the public portal are retained by the authors and/or other copyright owners and it is a condition of accessing publications that users recognise and abide by the legal requirements associated with these rights.

• Users may download and print one copy of any publication from the public portal for the purpose of private study or research.

- You may not further distribute the material or use it for any profit-making activity or commercial gain
- You may freely distribute the URL identifying the publication in the public portal

If you believe that this document breaches copyright please contact us providing details, and we will remove access to the work immediately and investigate your claim.

## Fabrication of Al-doped ZnO high aspect ratio nanowires and trenches as active components in mid-infrared plasmonics

<u>Evgeniy Shkondin<sup>1,2</sup></u>, Osamu Takayama<sup>2</sup>, Pernille Voss Larsen<sup>1</sup>, Mikkel Dysseholm Mar<sup>1</sup>, Flemming Jensen<sup>1</sup>, Andrei V. Lavrinenko<sup>2</sup>

<sup>1</sup>DTU Danchip, Kongens Lyngby, Denmark, <sup>2</sup>DTU Fotonik, Kongens Lyngby, Denmark

Fabrication of Al-doped ZnO high aspect ratio nanowires and trenches as active components in mid-infrared plasmonics

Al doped ZnO (AZO) is a promising alternative plasmonic material with tunable optical and electrical properties in a wide range. AZO can be used as a plasmonic component in optical metamaterials where it can exhibit near-epsilon-zero regime and hyperbolic dispersion in the near and middle infrared region. Most studied metamaterial geometries include multilayers and pillars. Despite many existing techniques for AZO synthesis, only atomic layer deposition (ALD) will allow conformal coatings of high aspect ratio structures. This work demonstrates a method of pattering AZO high aspect ratio nanogratings and pillars on silicon substrates.

AZO has been synthetized using DEZ (diethylzinc), TMA (trimethylaluminum) and deionized water. Different AI doping in AZO has been achieved by placing a single TMA-water cycle in "n" DEZ-water cycles, where n was varied from 5 to 35.

Prior to device fabrication, AZO films with different AI concentration has been grown on flat Si (100) substrates in the temperature range of 150°C-250°C and physical, optical and electrical properties have been investigated. The applied characterization techniques include four point probe resistivity measurements, atomic force microscopy (AFM), scanning electron microscopy (SEM), X-ray photoelectron spectroscopy (XPS), X-ray diffraction (XRD), and spectroscopic ellipsometry (SE).

Conventional deep-UV lithography was implemented for defining the gratings (lines with 400 nm pitch) and hole patterns (dots in a square lattice, with pitches of 400 and 500nm) on 2 cm2 scale chips. Thereafter, deep reactive ion etching was used to fabricate holes or trenches in silicon with a depth of 3  $\mu$ m for trenches and 2  $\mu$ m for holes. AZO with Al/ZnO cycle ratio 1:20 has been deposited on a prepared silicon template at the temperature of 200°C. The top part of AZO has been removed using Ar+ ion beam etching, so the silicon core gets exposed. At the end the silicon between the AZO trenches or pillars has been removed by SF6 plasma flow using reactive ion etching. Figure 1 and 2 shows fabricated freestanding AZO pillars and trenches as the final result.

Figur 1. AZO pillars Figur 2. AZO trenches. (Cross-section view)

